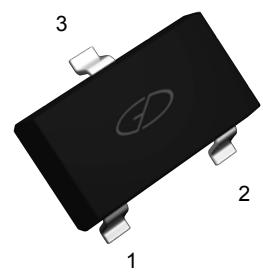


Features

- NPN transistor, Complementary Type MMBT3906

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	200	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance Junction To Ambient	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to +150	$^\circ\text{C}$



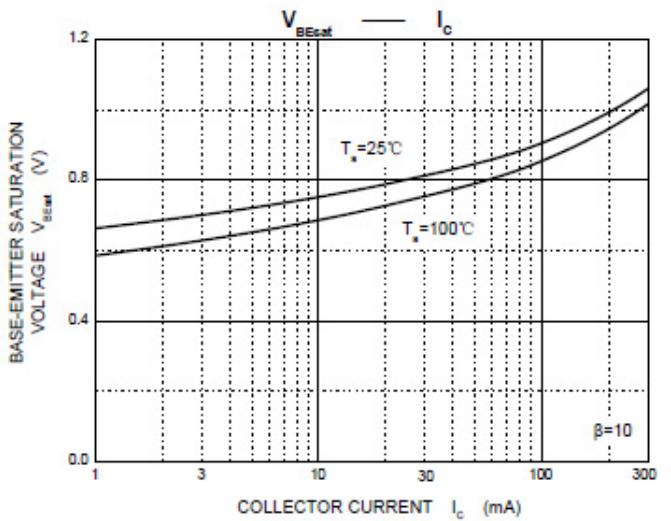
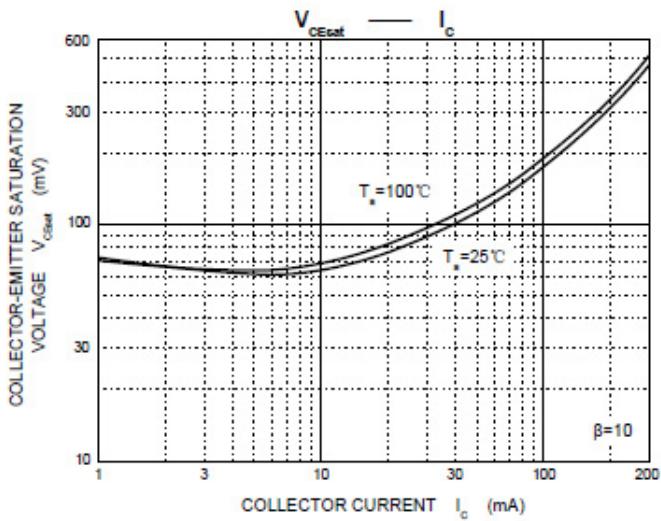
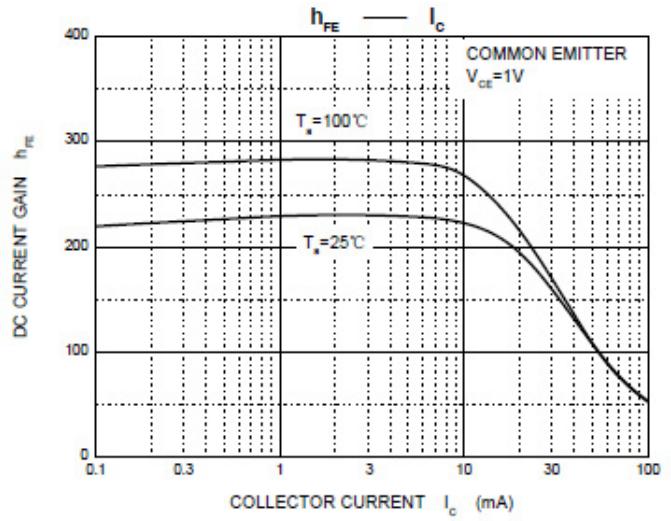
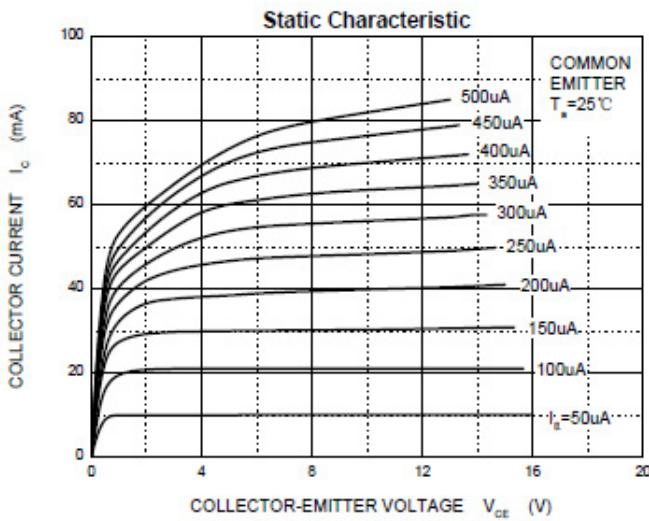
Package: SOT-23

1. BASE
2. Emitter
3. Collector

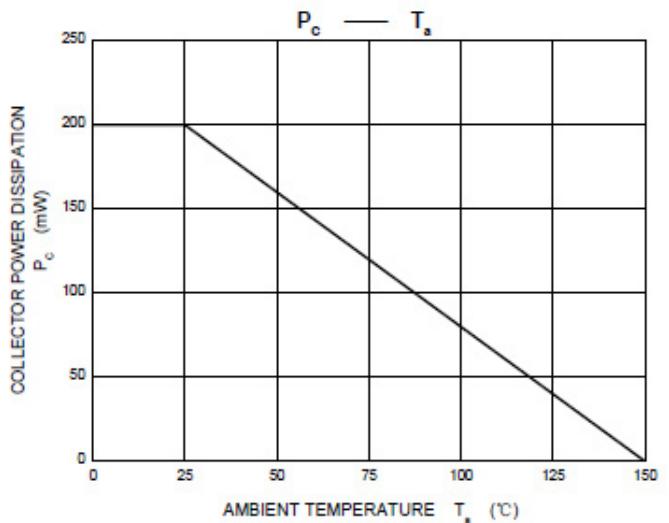
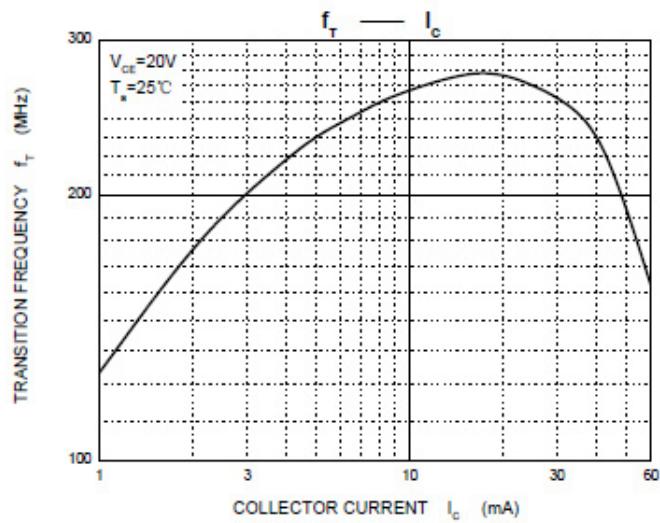
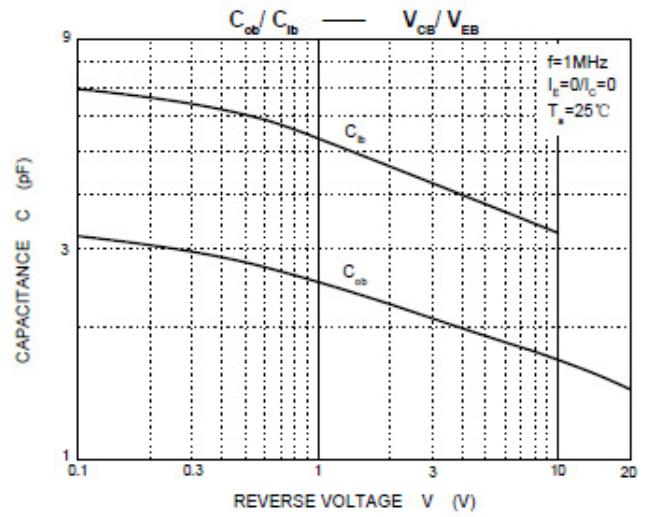
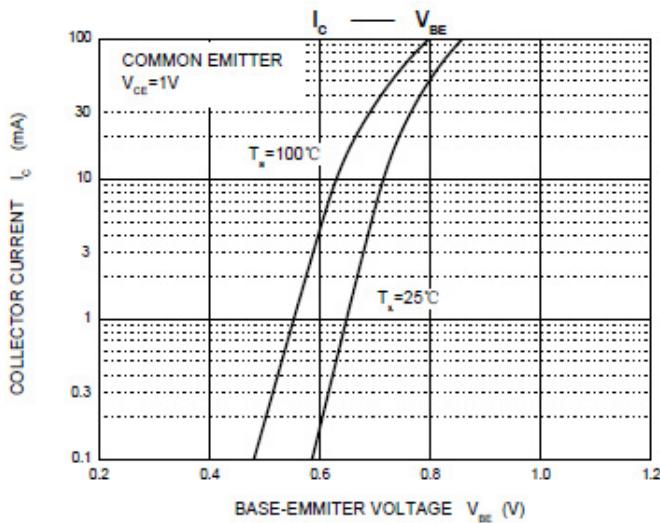
Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Collector-base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	60	--	V
Collector-emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	40	--	V
Emitter-base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6	--	V
Collector Cut-off Current	I_{CEX}	$V_{CE}=30\text{V}, V_{EB(\text{off})}=3\text{V}$	--	50	nA
Collector Cut-off Current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$	--	100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$	--	100	nA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=10\text{mA}$	100	300	
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=50\text{mA}$	60	--	
	$h_{FE(3)}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	30	--	
Collector-emitter Saturation Voltage	$V_{CE(\text{sat})}$	$I_C=50\text{mA}, I_B=5\text{mA}$	--	0.3	V
Base-emitter Saturation Voltage	$V_{BE(\text{sat})}$	$I_C=50\text{mA}, I_B=5\text{mA}$	--	0.95	V
Transition Frequency	f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	300	--	MHz
Delay Time	t_d	$V_{CC}=3\text{V}, V_{BE(\text{off})}=-0.5\text{V} I_C=10\text{mA}, I_{B1}=1\text{mA}$	--	35	nS
Rise Time	t_r	$V_{CC}=3\text{V}, V_{BE(\text{off})}=-0.5\text{V} I_C=10\text{mA}, I_{B1}=1\text{mA}$	--	35	nS
Storage Time	t_s	$V_{CC}=3\text{V}, I_C=10\text{mA}, I_{B1}=I_{B2}=1\text{mA}$	--	200	nS
Fall Time	t_f	$V_{CC}=3\text{V}, I_C=10\text{mA}, I_{B1}=I_{B2}=1\text{mA}$	--	50	nS

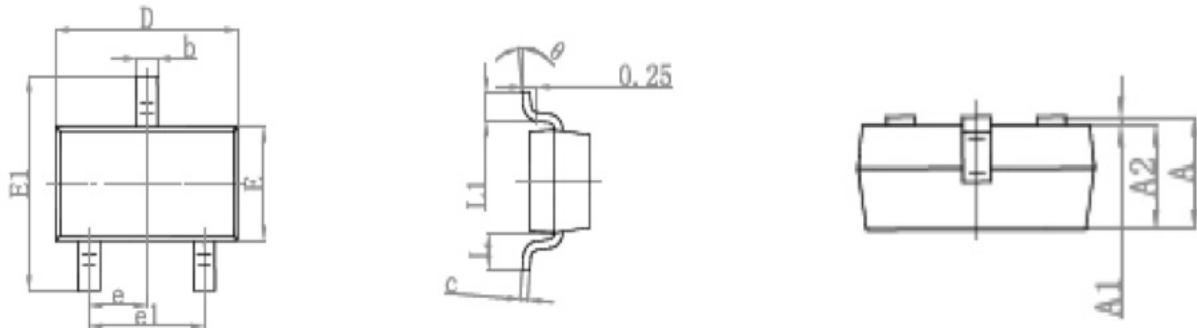
Typical Electrical Characteristic Curves



Typical Electrical Characteristic Curves

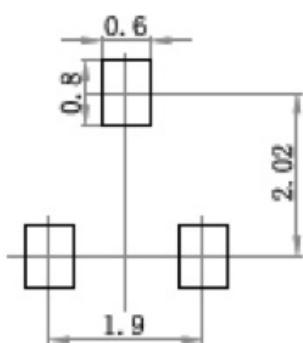


Package Outline Dimensions SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.